

Silicon NPN Power Transistors

2SC3892**DESCRIPTION**

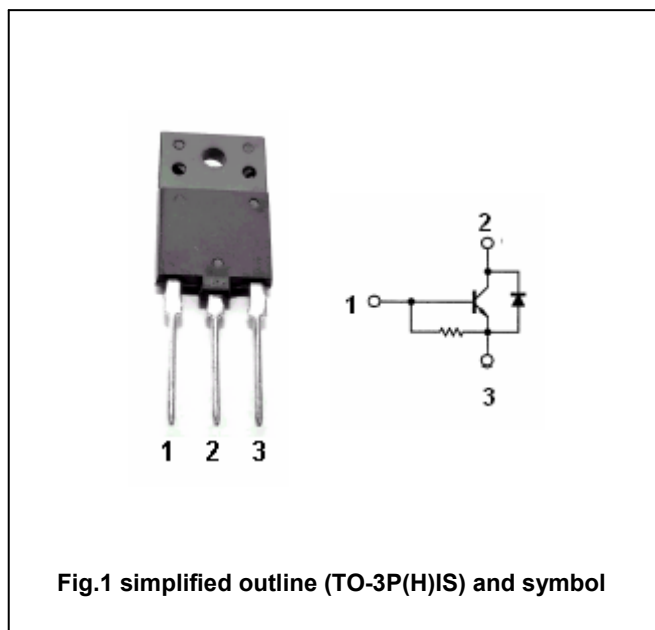
- With TO-3P(H)IS package
- Built-in damper diode
- High voltage ,high speed

APPLICATIONS

- Horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

**Absolute maximum ratings (Ta=25)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1400	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		7	A
I_{CM}	Collector current-peak		14	A
I_B	Base current		3.5	A
P_C	Collector power dissipation	$T_C=25$	50	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=200mA$, $I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A$; $I_B=1.2A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A$; $I_B=1.2A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=500V$; $I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$	66		200	mA
h_{FE}	DC current gain	$I_C=1A$; $V_{CE}=5V$	8	12		
f_T	Transition frequency	$I_C=0.1A$; $V_{CE}=10V$	1	3		MHz
C_{OB}	Collector output capacitance	$I_E=0$; $V_{CB}=10V$; $f=1MHz$		210		pF
V_F	Diode forward voltage	$I_F=5A$			2.0	V
t_s	Storage time	Resistive load $I_{CP}=5A$; $I_{B1}=1A$; $I_{B2}=-2A$; $R_L=40\Omega$			2.5	μs
t_f	Fall time				0.2	μs

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PACKAGE OUTLINE

